

IRHLUB770Z4 (JANSR2N7616UB)

PD-95813N

Radiation Hardened Logic Level Power MOSFET
Surface Mount (UB)
60V, 0.8A, N-channel, R7 Technology

Features

- 5V CMOS and TTL compatible
- Single event effect (SEE) hardened
- Fast switching
- Low total gate charge
- Simple drive requirements
- Hermetically sealed
- Light weight
- Surface mount
- ESD rating: Class 0B per MIL-STD-750, Method 1020

Product Summary

- **BV_{DSS}**: 60V
- **I_D**: 0.8A
- **R_{DS(on), max}**: 0.68Ω
- **Q_{G, max}**: 3.6nC
- **REF**: MIL-PRF-19500/744

Potential Applications

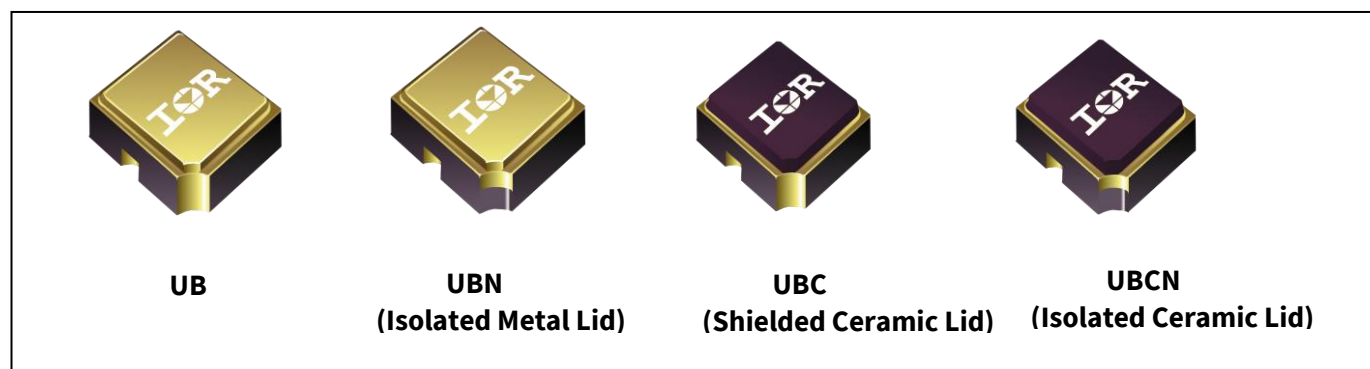
- DC-DC converter
- Motor drives

Product Validation

Qualified according to MIL-PRF-19500 for space applications

Description

IR HiRel R7 Logic Level Power MOSFETs provide simple solution to interfacing CMOS and TTL control circuits to power devices in space and other radiation environments. The threshold voltage remains within acceptable operating limits over the full operating temperature and post radiation. This is achieved while maintaining single event gate rupture and single event burnout immunity. The device is ideal when used to interface directly with most logic gates, linear IC's, micro-controllers, and other device types that operate from a 3.3-5V source. It may also be used to increase the output current of a PWM, voltage comparator or an operational amplifier where the logic level drive signal is available.



Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Ordering Information

Ordering Information

Table 1 **Ordering options**

Part number	Package	Screening Level	TID Level
IRHLUB770Z4	UB	COTS	100 krad(Si)
JANSR2N7616UB	UB	JANS	100 krad(Si)
IRHLUB730Z4	UB	COTS	300 krad(Si)
JANSF2N7616UB	UB	JANS	300 krad(Si)
IRHLUBN770Z4	UBN	COTS	100 krad(Si)
JANSR2N7616UBN	UBN	JANS	100 krad(Si)
IRHLUBN730Z4	UBN	COTS	300 krad(Si)
JANSF2N7616UBN	UBN	JANS	300 krad(Si)
IRHLUBC770Z4	UBC	COTS	100 krad(Si)
JANSR2N7616UBC	UBC	JANS	100 krad(Si)
IRHLUBC730Z4	UBC	COTS	300 krad(Si)
JANSF2N7616UBC	UBC	JANS	300 krad(Si)
IRHLUBCN770Z4	UBCN	COTS	100 krad(Si)
JANSR2N7616UBCN	UBCN	JANS	100 krad(Si)
IRHLUBCN730Z4	UBCN	COTS	300 krad(Si)
JANSF2N7616UBCN	UBCN	JANS	300 krad(Si)

IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

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Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
$I_{D1} @ V_{GS} = 4.5V, T_C = 25^{\circ}C$	Continuous Drain Current	0.8	A
$I_{D2} @ V_{GS} = 4.5V, T_C = 100^{\circ}C$	Continuous Drain Current	0.5	A
$I_{DM} @ T_C = 25^{\circ}C$	Pulsed Drain Current ¹	3.2	A
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	0.6	W
	Linear Derating Factor	0.005	W/ $^{\circ}C$
V_{GS}	Gate-to-Source Voltage	± 10	V
E_{AS}	Single Pulse Avalanche Energy ²	26.6	mJ
I_{AR}	Avalanche Current ¹	0.8	A
E_{AR}	Repetitive Avalanche Energy ¹	0.06	mJ
dv/dt	Peak Diode Reverse Recovery ³	4.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$
	Lead Temperature	300 (for 5s)	
	Weight	43 (Typical)	mg

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.² $V_{DD} = 25V$, starting $T_J = 25^{\circ}C$, $L = 83mH$, Peak $I_L = 0.8A$, $V_{GS} = 10V$ ³ $I_{SD} \leq 0.8A$, $di/dt \leq 130A/\mu s$, $V_{DD} \leq 60V$, $T_J \leq 150^{\circ}C$

Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics (Pre-Irradiation)

Table 3 Static and Dynamic Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temp. Coefficient	—	0.07	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.68	Ω	$V_{GS} = 4.5V, I_{D2} = 0.5A^1$
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_j$	Gate Threshold Voltage Coefficient	—	-4.04	—	mV/ $^\circ\text{C}$	
G_{fs}	Forward Transconductance	0.23	—	—	S	$V_{DS} = 10V, I_{D2} = 0.5A^1$
I_{DSS}	Zero Gate Voltage Drain Current	—	—	1.0	μA	$V_{DS} = 48V, V_{GS} = 0V$
		—	—	10		$V_{DS} = 48V, V_{GS} = 0V, T_j = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 10V$
	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -10V$
Q_G	Total Gate Charge	—	—	3.6	nC	$I_{D1} = 0.8A$ $V_{DS} = 30V$ $V_{GS} = 4.5V$
Q_{GS}	Gate-to-Source Charge	—	—	1.5		
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	1.8		
$t_{d(on)}$	Turn-On Delay Time	—	—	8.0	ns	$I_{D1} = 0.8A^{**}$ $V_{DD} = 30V$ $R_G = 24\Omega$ $V_{GS} = 5.0V$
t_r	Rise Time	—	—	24		
$t_{d(off)}$	Turn-Off Delay Time	—	—	30		
t_f	Fall Time	—	—	12		
$L_s + L_D$	Total Inductance	—	8.4	—	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	—	166	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	42	—		
C_{rss}	Reverse Transfer Capacitance	—	3.5	—		
R_G	Gate Resistance	—	9.5	—	Ω	$f = 1.0\text{MHz}$, open drain

** Switching speed maximum limits are based on manufacturing test equipment and capability.

¹ Pulse width $\leq 300\mu s$; Duty Cycle $\leq 2\%$

Device Characteristics

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	0.8	A	
I _{SM}	Pulsed Source Current (Body Diode) ¹	—	—	3.2	A	
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 0.8 A, V _{GS} = 0V ²
t _{rr}	Reverse Recovery Time	—	—	78	ns	T _J = 25°C, I _F = 0.8A, V _{DD} ≤ 25V di/dt = 100A/μs ²
Q _{rr}	Reverse Recovery Charge	—	44	—	nC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient	—	—	200	$^\circ\text{C}/\text{W}$
$R_{\theta JL}$	Junction-to-Lead	—	—	40	

2.4 Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 3 and 4) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

2.4.1 Electrical Characteristics — Post Total Dose Irradiation

Table 6 Electrical Characteristics @ $T_J = 25^\circ\text{C}$, Post Total Dose Irradiation ^{3, 4}

Symbol	Parameter	Up to 300 krad (Si) ⁵		Unit	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	—	V	$V_{GS} = 0\text{ V}$, $I_D = 250\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	1.0	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	$V_{GS} = 10\text{ V}$
	Gate-to-Source Leakage Reverse	—	-100		$V_{GS} = -10\text{ V}$
I_{DSS}	Zero Gate Voltage Drain Current	—	1.0	μA	$V_{DS} = 48\text{ V}$, $V_{GS} = 0\text{ V}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-39) ²	—	0.65	Ω	$V_{GS} = 4.5\text{ V}$, $I_{D2} = 0.5\text{ A}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (UB) ²	—	0.68	Ω	$V_{GS} = 4.5\text{ V}$, $I_{D2} = 0.5\text{ A}$
V_{SD}	Diode Forward Voltage	—	1.2	V	$V_{GS} = 0\text{ V}$, $I_F = 0.8\text{ A}$

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.

² Pulse width $\leq 300\mu\text{s}$; Duty Cycle $\leq 2\%$

³ Total Dose Irradiation with V_{GS} Bias. $V_{GS} = 10\text{ V}$ applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁴ Total Dose Irradiation with V_{DS} Bias. $V_{DS} = 48\text{ V}$ applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁵ Part numbers: IRHLUB770Z4 (JANSR2N7616UB), IRHLUB730Z4 (JANSF2N7616UB), IRHLUBN770Z4 (JANSR2N7616UBN), IRHLUBN730Z4 (JANSF2N7616UBN), IRHLUBC770Z4 (JANSR2N7616UBC), IRHLUBC730Z4 (JANSF2N7616UBC), IRHLUBCN770Z4 (JANSR2N7616UBCN), IRHLUBCN730Z4 (JANSF2N7616UBCN)

IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Device Characteristics

2.4.2 Single Event Effects — Safe Operating Area

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. 1 and Table 7.

Table 7 Typical Single Event Effects Safe Operating Area

LET (MeV·cm ² /mg)	Energy (MeV)	Range (μm)	V _{DS} (V)				
			V _{GS} = 0V	V _{GS} = -2V	V _{GS} = -4V	V _{GS} = -5V	V _{GS} = -6V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	60	60	60	60	60
62 ± 5%	355 ± 7.5%	33 ± 7.5%	60	60	60	60	—
85 ± 5%	380 ± 7.5%	29 ± 7.5%	60	60	60	—	—

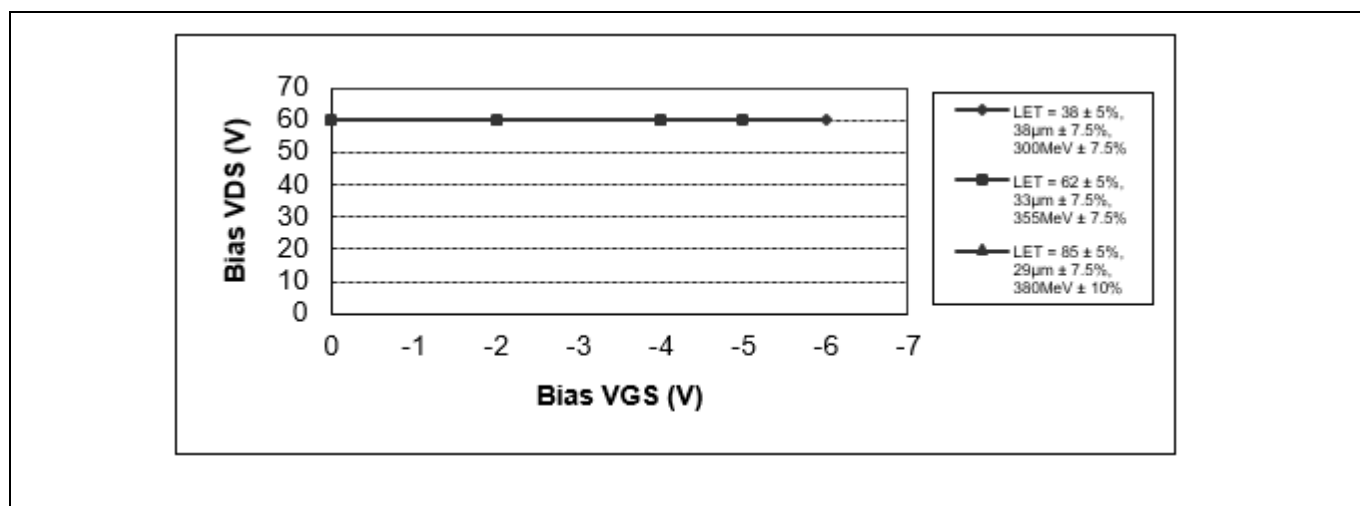


Figure 1 Typical Single Event Effect, Safe Operating Area

IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Electrical Characteristics Curves (Pre-irradiation)

3 Electrical Characteristics Curves (Pre-irradiation)

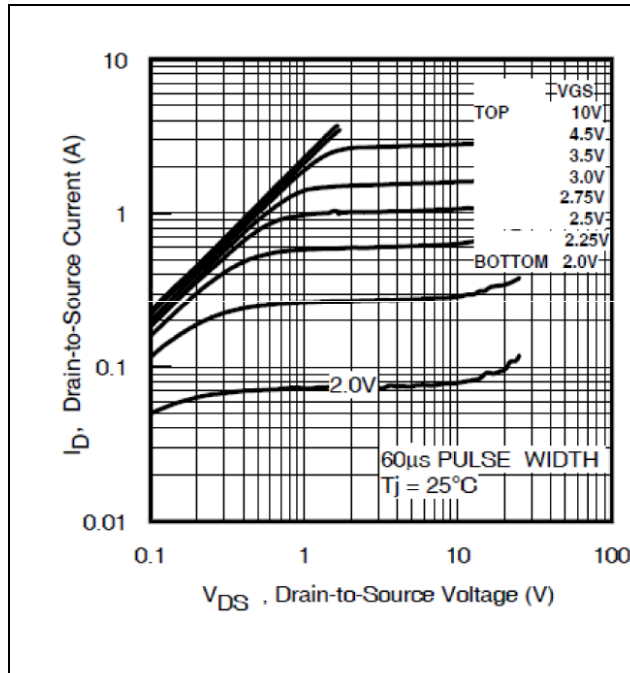


Figure 2 Typical Output Characteristics

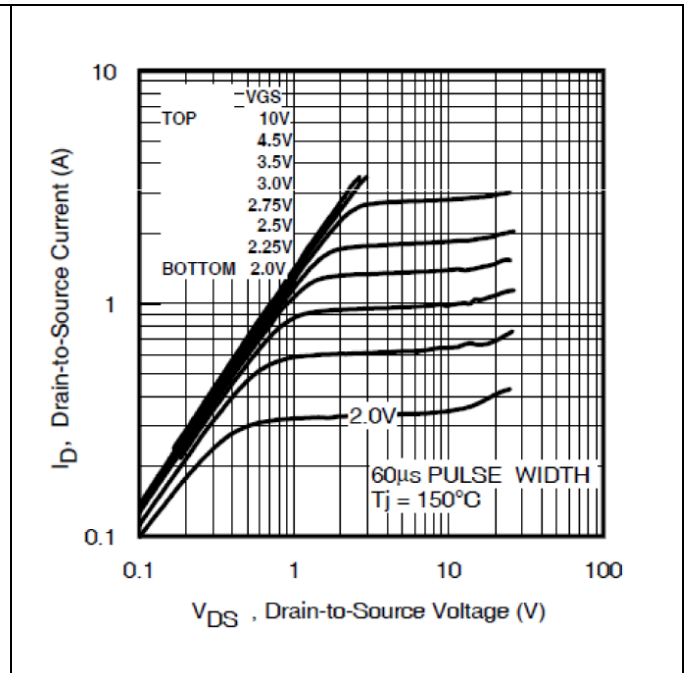


Figure 3 Typical Output Characteristics

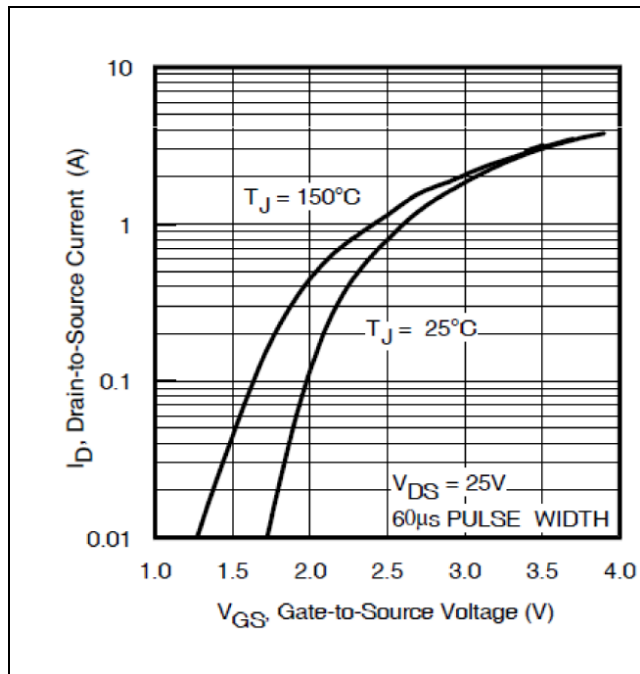


Figure 4 Typical Transfer Characteristics

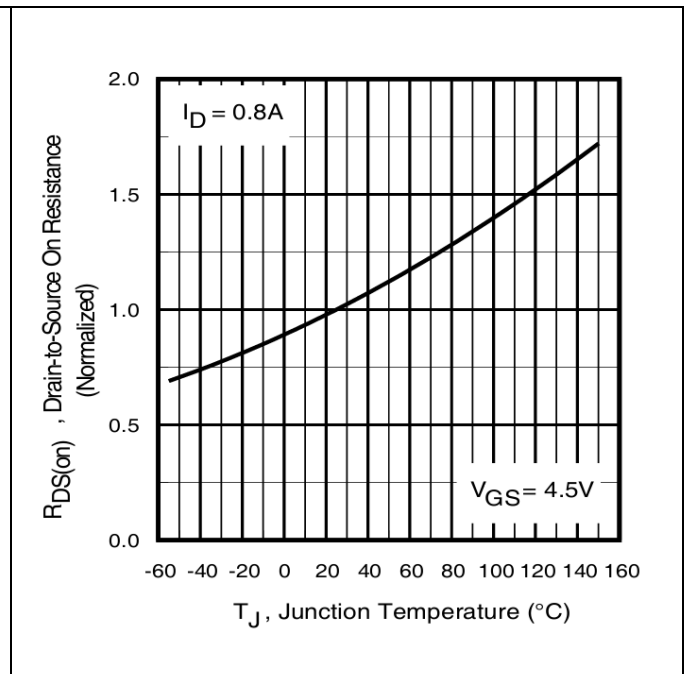


Figure 5 Normalized On-Resistance Vs. Temperature

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Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Electrical Characteristics Curves (Pre-irradiation)

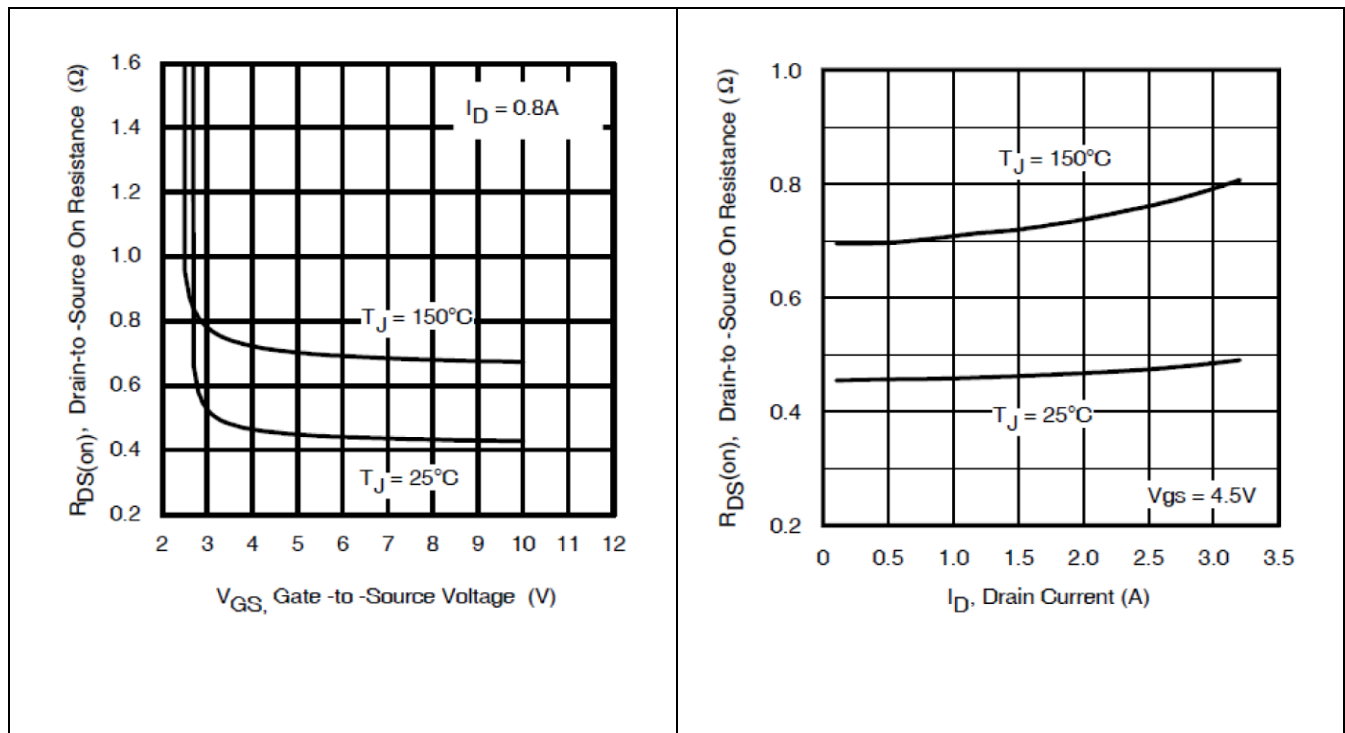


Figure 6 Typical On-Resistance Vs. Gate Voltage

Figure 7 Typical On-Resistance Vs. Drain Current

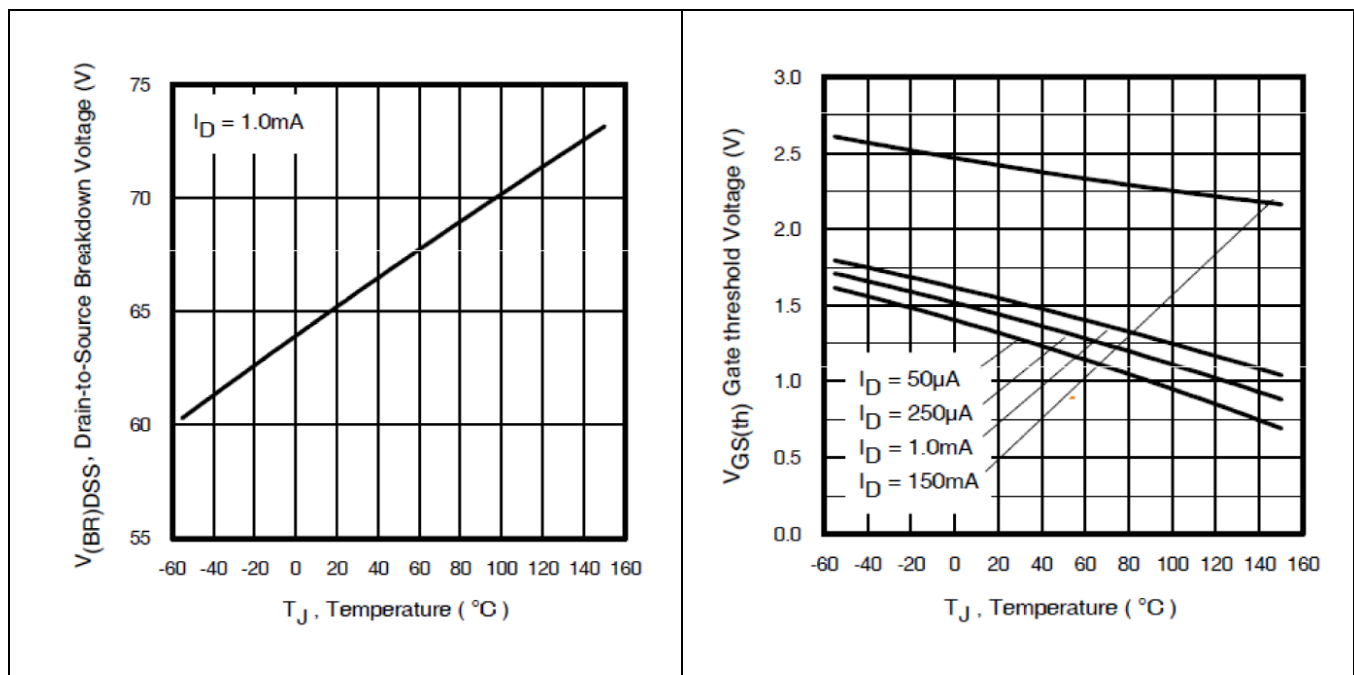


Figure 8 Typical Drain-to-Source Breakdown Voltage Vs. Temperature

Figure 9 Typical Threshold Voltage Vs. Temperature

IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Electrical Characteristics Curves (Pre-irradiation)

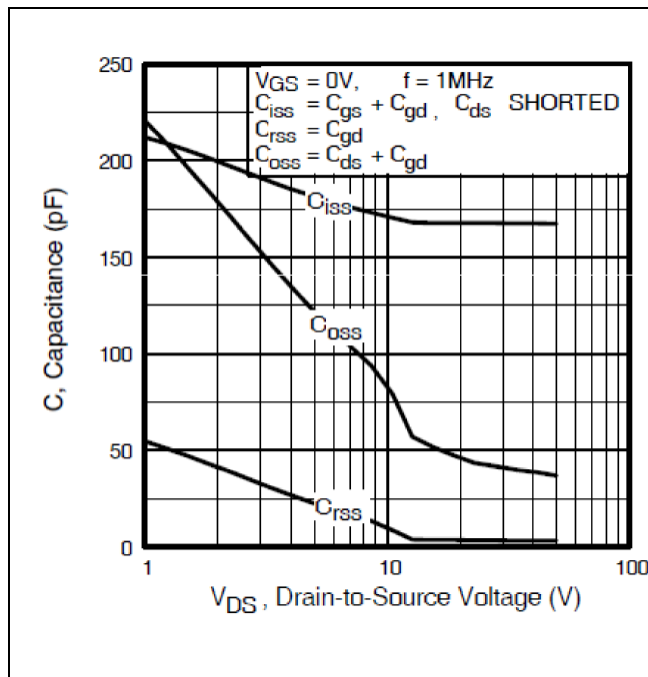


Figure 10 Typical Capacitance Vs. Drain-to-Source Voltage

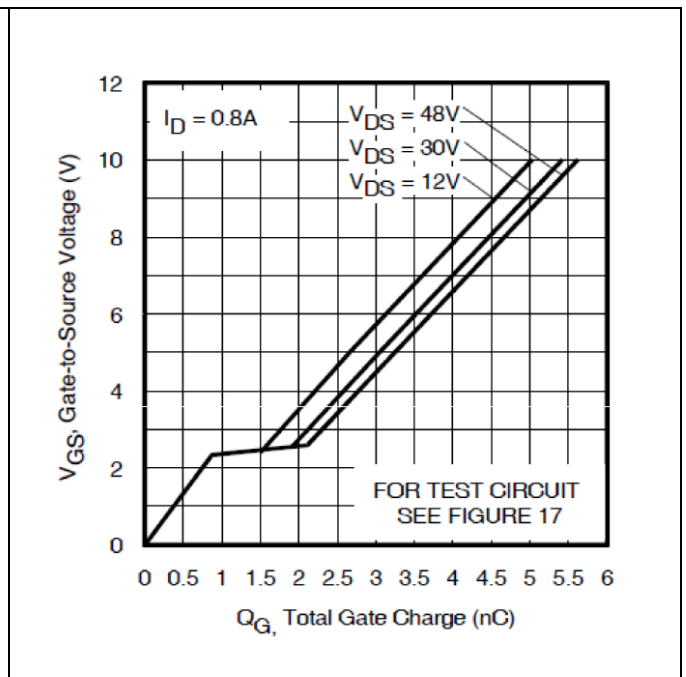


Figure 11 Gate-to-Source Voltage Vs. Typical Gate Charge

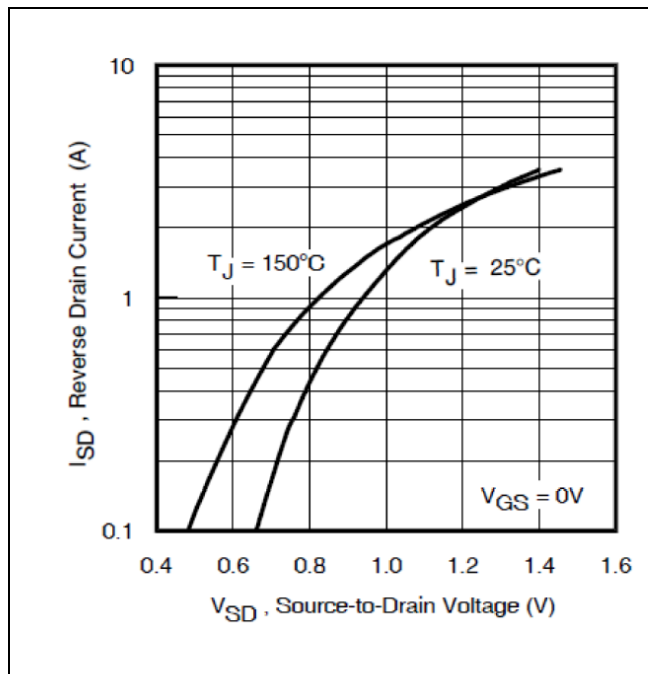


Figure 12 Typical Source-Drain Current Vs. Diode Forward Voltage

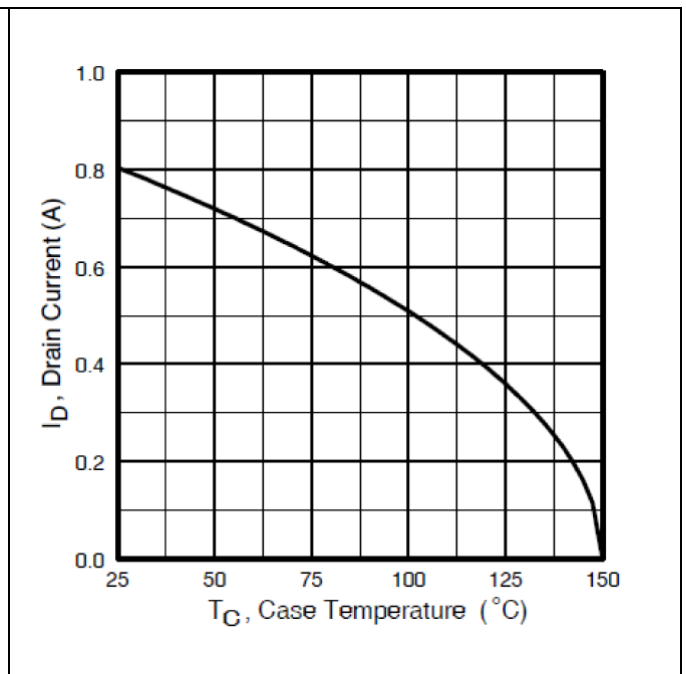


Figure 13 Maximum Drain Current Vs. Case Temperature

IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Electrical Characteristics Curves (Pre-irradiation)

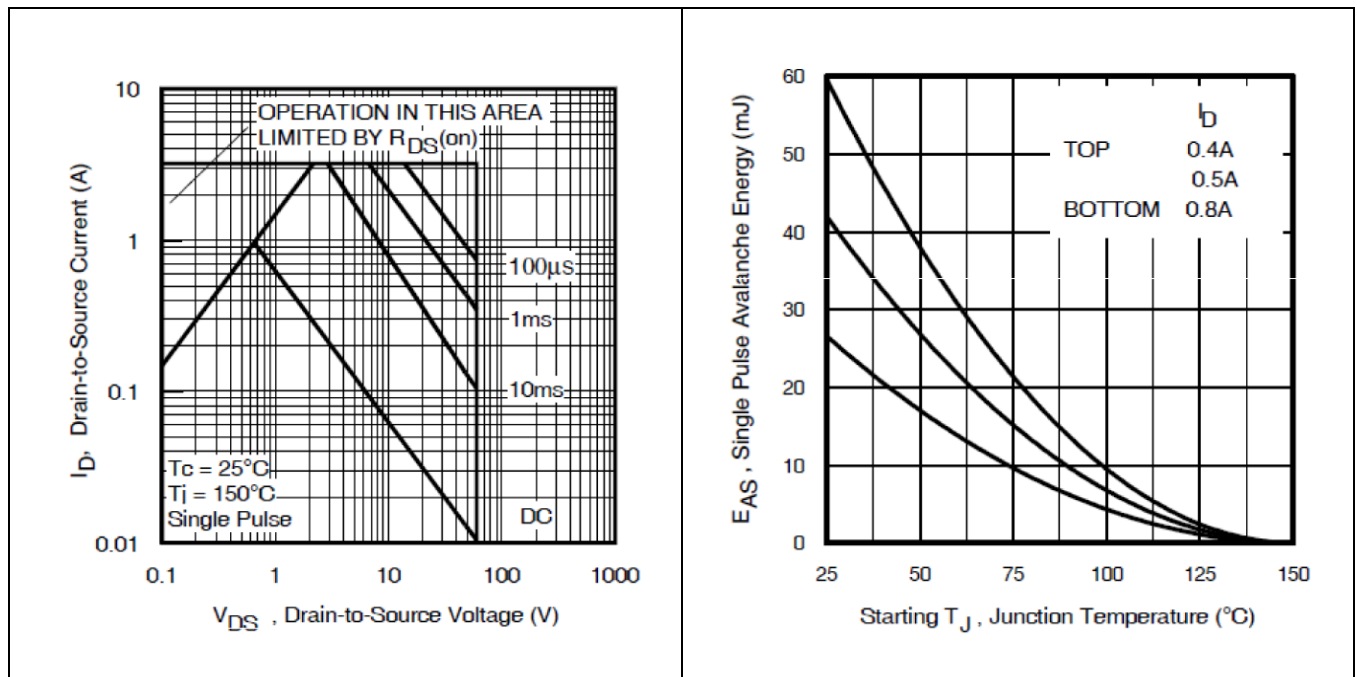


Figure 14 Maximum Safe Operating Area

Figure 15 Maximum Avalanche Energy Vs. Junction Temperature

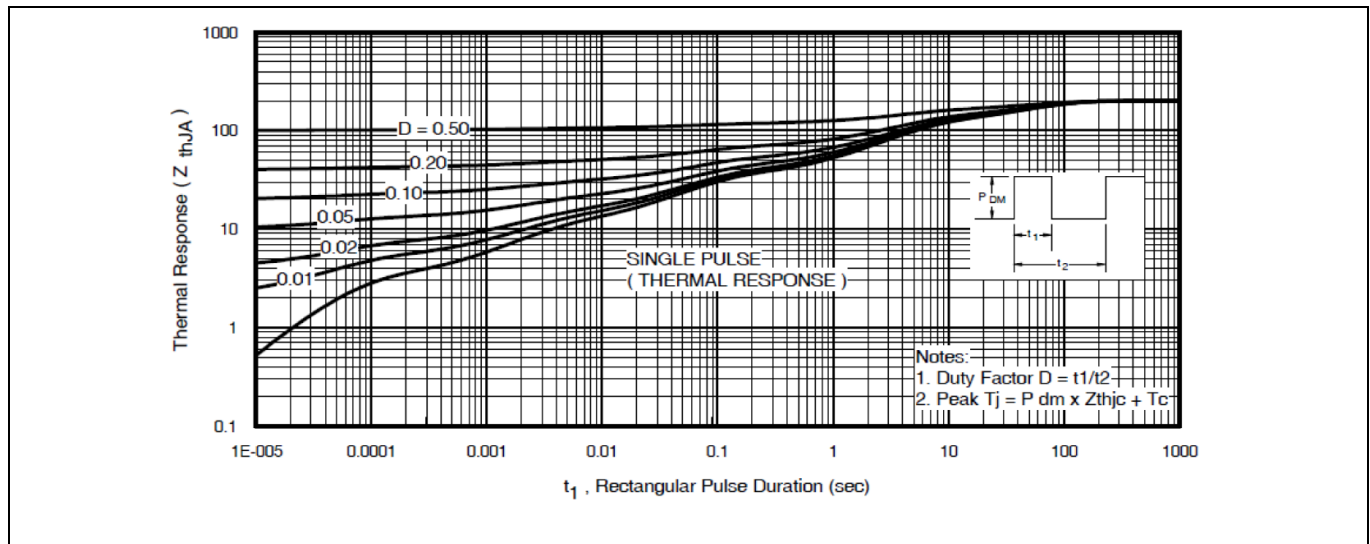


Figure 16 Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Test Circuits (Pre-irradiation)

4 Test Circuits (Pre-irradiation)

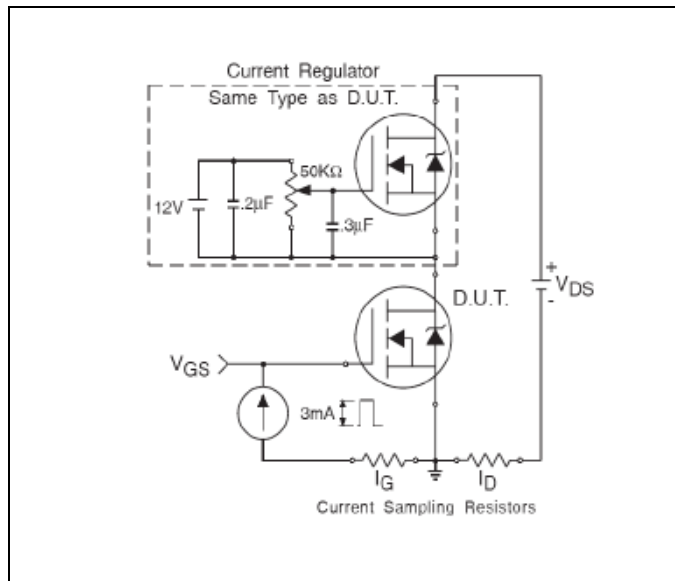


Figure 17 Gate Charge Test Circuit

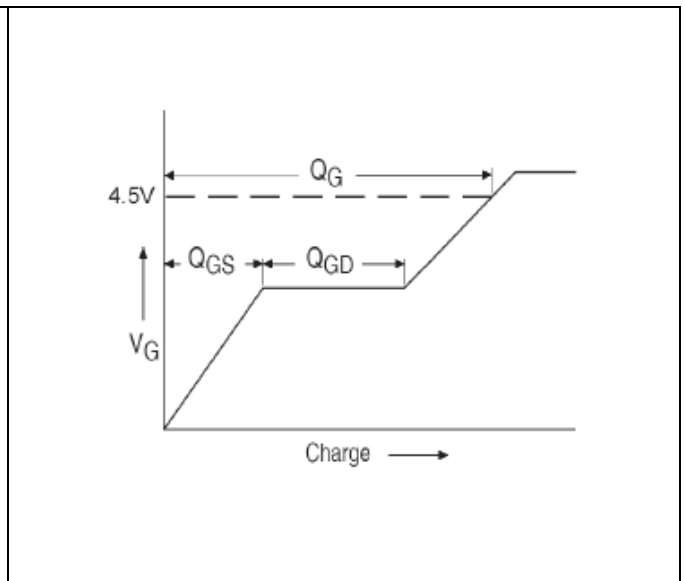


Figure 18 Gate Charge Waveform

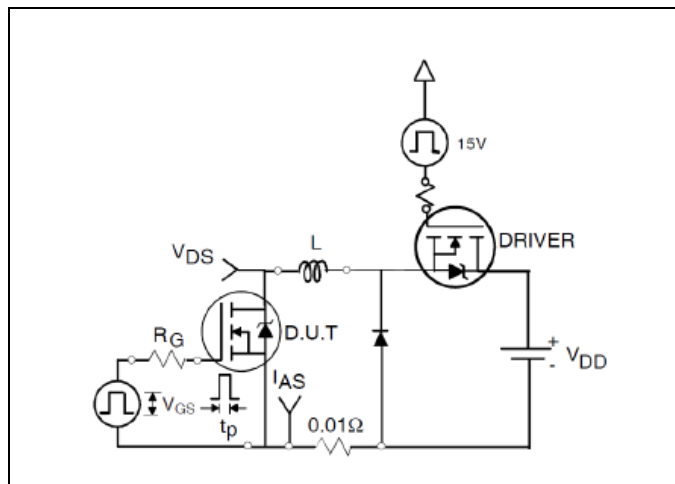


Figure 19 Unclamped Inductive Test Circuit

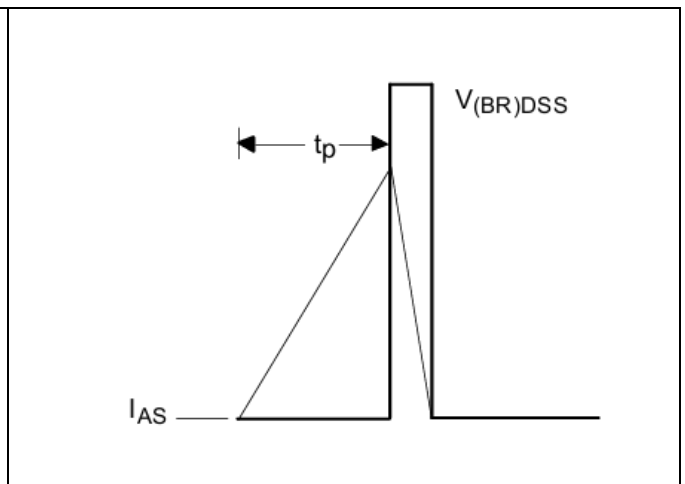


Figure 20 Unclamped Inductive Waveform

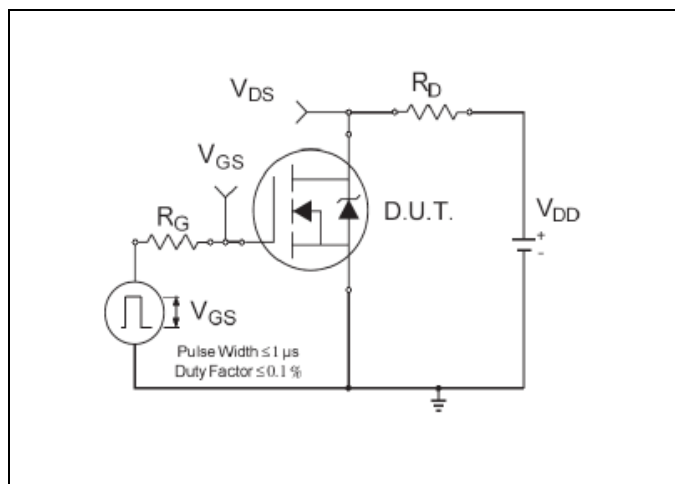


Figure 21 Switching Time Test Circuit

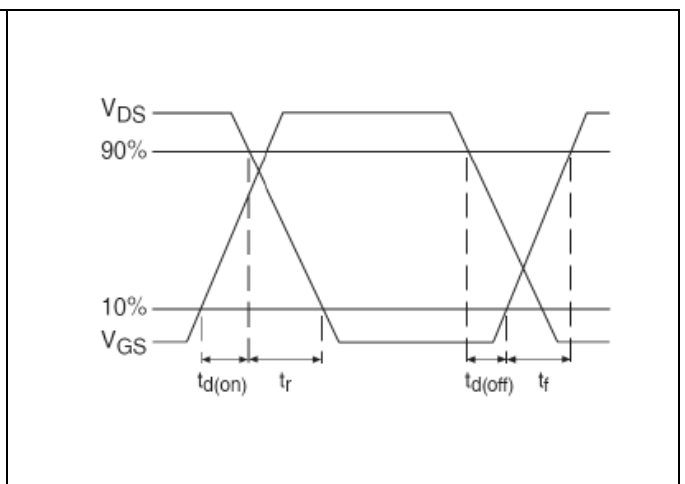


Figure 22 Switching Time Waveforms

IRHLUB770Z4 (JANSR2N7616UB)

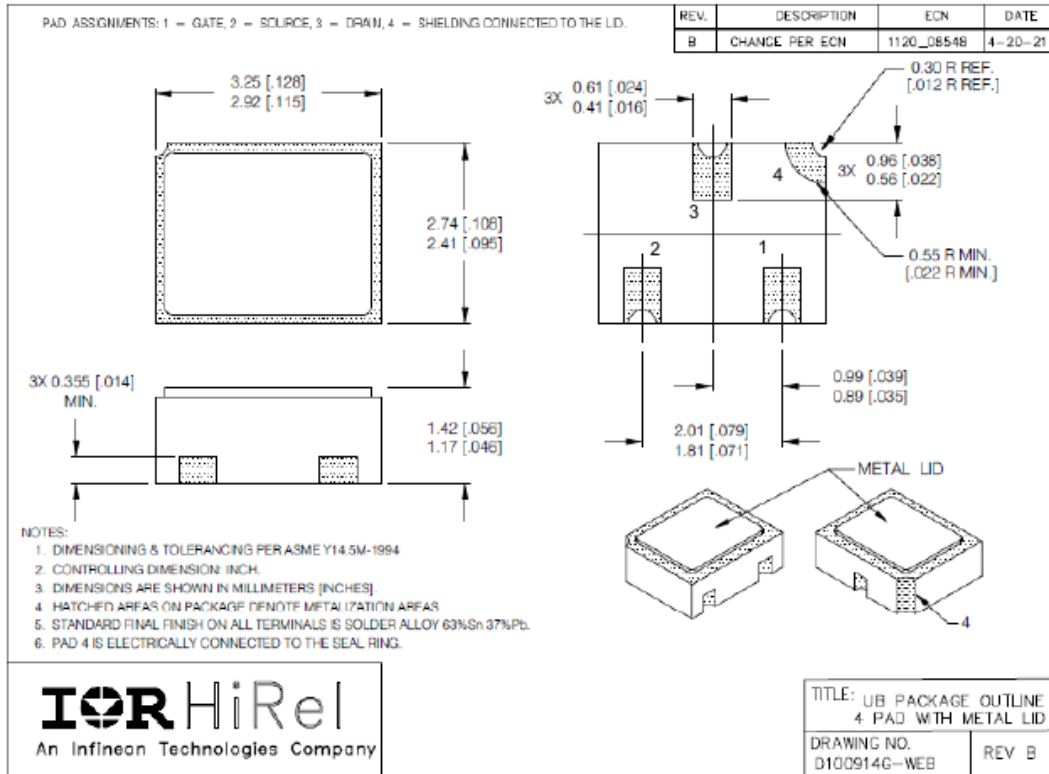
Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Package Outline

5 Package Outline

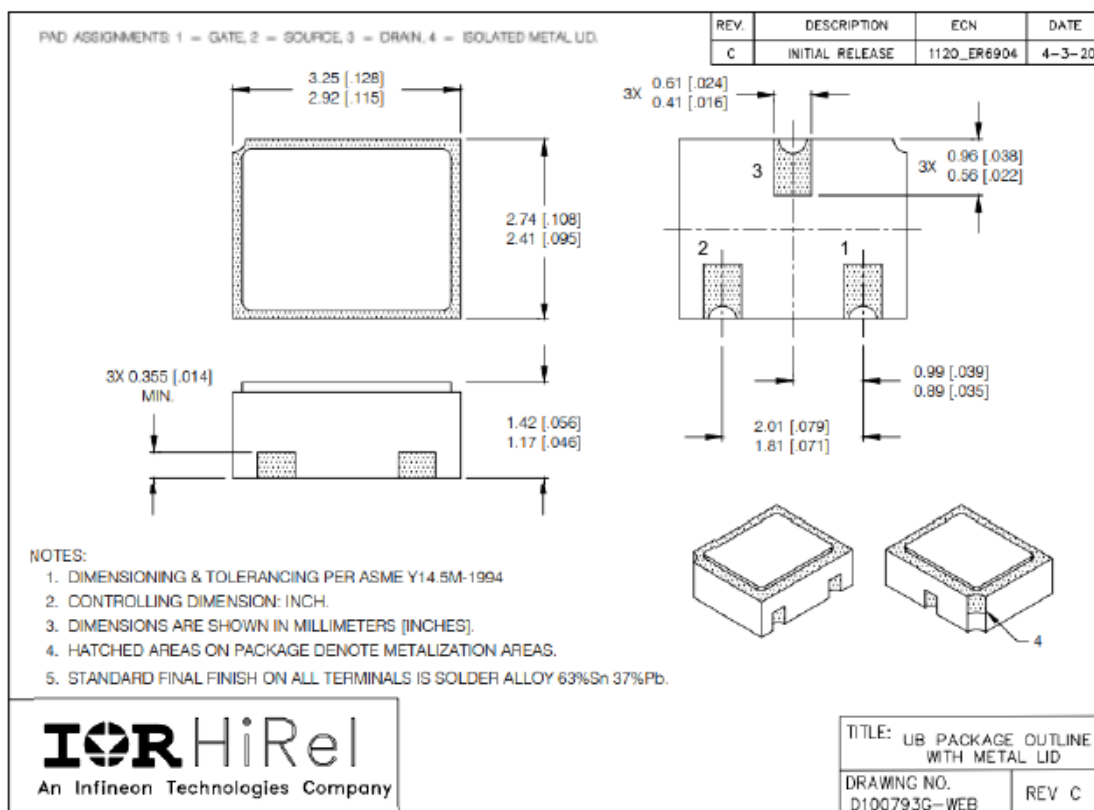
Note: For the most updated package outline, please see the website: [UB](#)

Case Outline and Dimensions - UB (Shielded Metal Lid Connected to 4th Pad)



Note: For the most updated package outline, please see the website: [UBN](#)

Case Outline and Dimensions - UBN (Isolated Metal Lid, No 4th Pad)



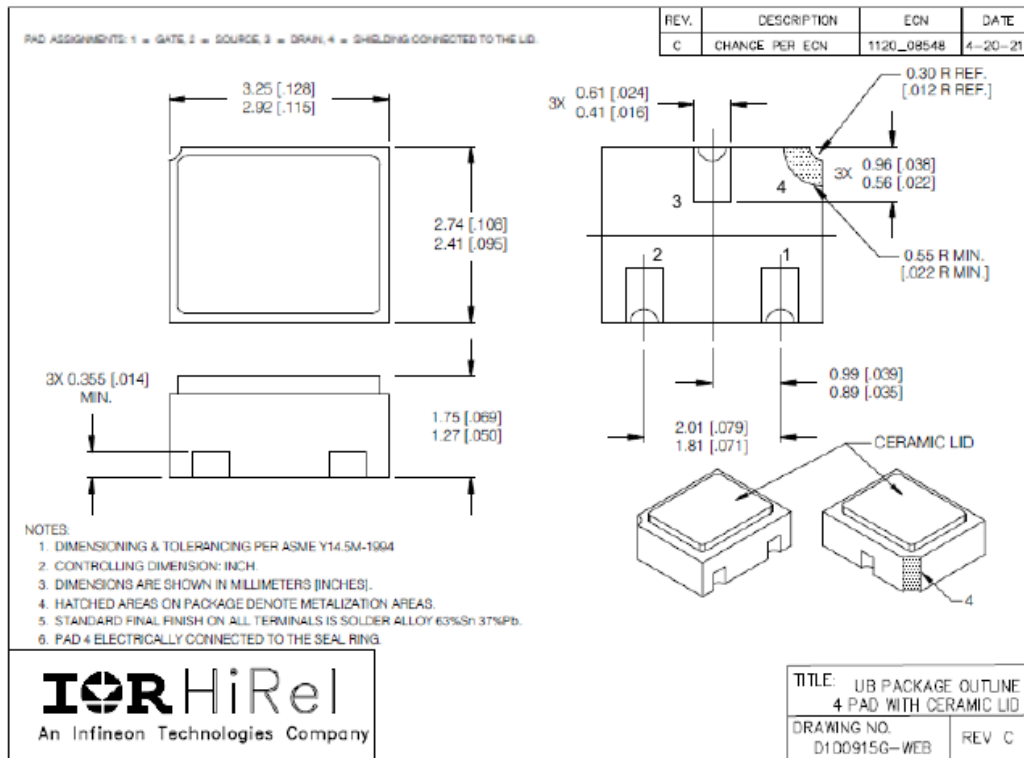
IRHLUB770Z4 (JANSR2N7616UB)

Radiation Hardened Logic Level Power MOSFET Surface-Mount (UB)

Package Outline

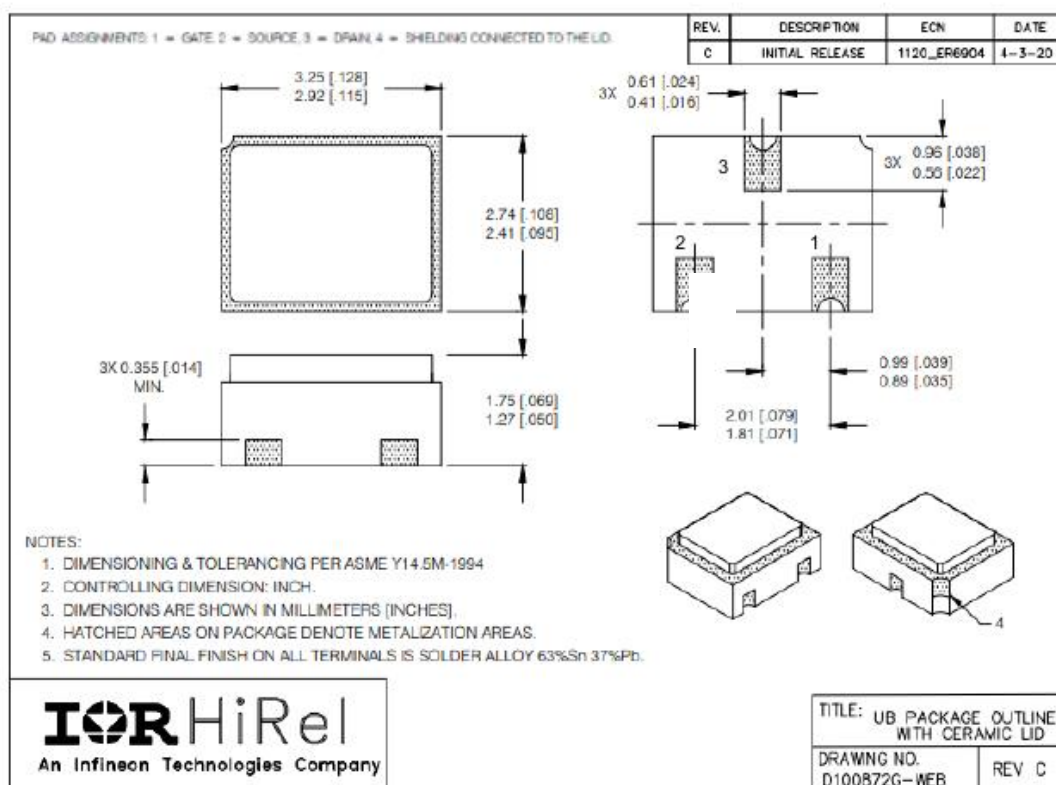
Note: For the most updated package outline, please see the website: [UBC](#)

Case Outline and Dimensions - UBC (Shielded Ceramic Lid Connected to 4th Pad)



Note: For the most updated package outline, please see the website: [UBCN](#)

Case Outline and Dimensions - UBCN (Isolated Ceramic Lid, No 4th Pad)



Revision history**Revision history**

Document version	Date of release	Description of changes
	02/03/2004	Datasheet (PD-95813)
Rev A	09/03/2004	Updated based on ECN-12213
Rev B	09/09/2005	Updated based on ECN-13390
Rev C	01/31/2006	Deleted typo- "Available on tape and reel" from Feature – Page 1.
Rev D	06/11/2007	Added 2N7616UB designated number
Rev E	07/21/2009	Updated based on ECN-16472
Rev F	08/04/2009	Updated SEE table
Rev G	03/15/2010	Updated based on ECN-17155
Rev H	11/02/2012	Updated Fig10
Rev I	02/05/2019	Updated based on ECN-1120_05810
Rev J	01/10/2020	Updated based on ECN-1120_07601
Rev K	10/21/2020	Updated based on ECN-1120_08235
Rev L	04/27/2021	Updated based on ECN-1120_08548
Rev M	08/12/2022	Updated based on ECN-1120_09174
Rev N	09/08/2025	Updated based on ECN- Z8F80828229

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Edition 2025-09-08

Published by

**International Rectifier HiRel Products,
Inc.**

**An Infineon Technologies company
El Segundo, California 90245 USA**

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